

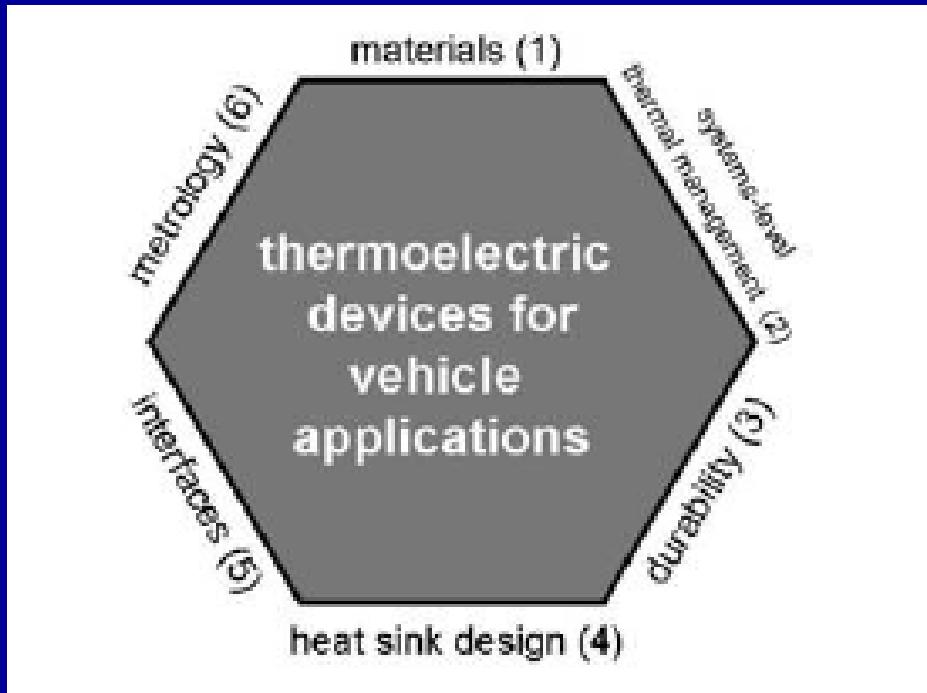
NSF/DOE Thermoelectrics Partnership: Thermoelectrics for Automotive Waste Heat Recovery

Xianfan Xu (ME), Timothy Fisher (ME), Stephen Heister
(AAE), Timothy Sands (MSE), Yue Wu (ChemE)

Purdue University
In Partnership with General Motors Global R&D
and Oak Ridge National Laboratory



NSF/DOE Targeted Areas

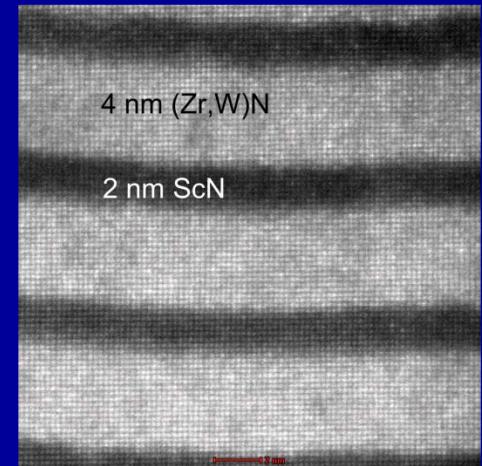
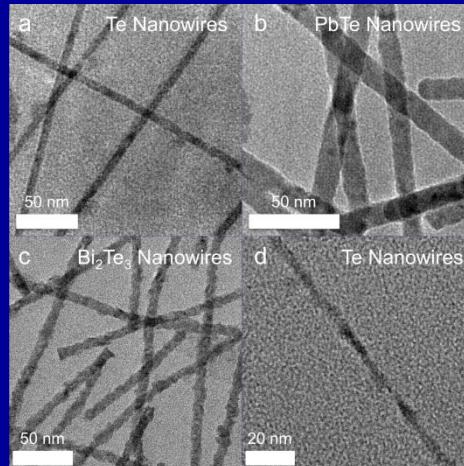
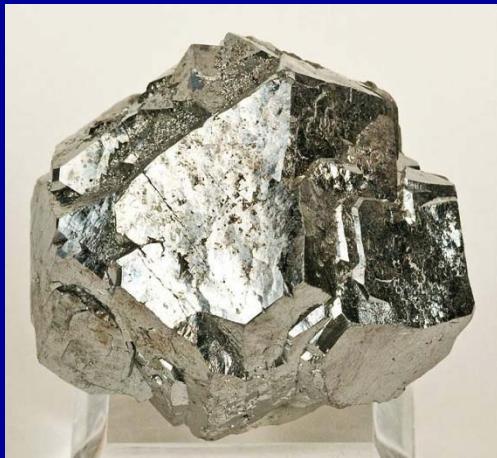


Focused areas of this proposal:

- TE Materials
- Heat sink - high temperature side heat exchanger
- Thermal interface materials
- Metrology

TE Materials

- Skutterudite (GM) ~ 500°C – advanced characterization on thermal conductivity reduction (Xu)
- Nanowires - room-mid temperature PbTe, Bi₂Te₃; and high temperature oxide nanowires (Wu)
- Metal-semiconductor superlattice (Sands)



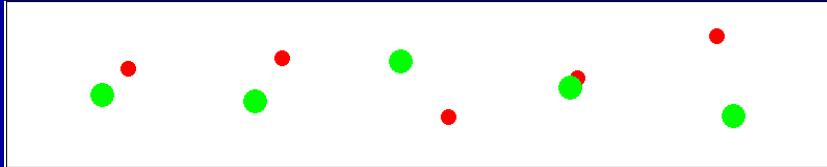
Advanced Characterization of TE Materials

Xianfan Xu

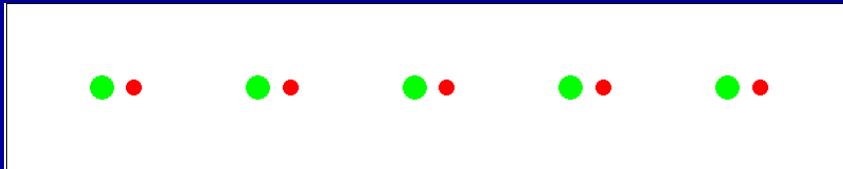
- Commonly used approach to increase ZT of TE materials is to reduce the lattice thermal conductivity
- We conduct femtosecond (10^{-15} s) time-resolved studies of phonon scattering in thermoelectric materials to understand the fundamentals of thermal conductivity reduction



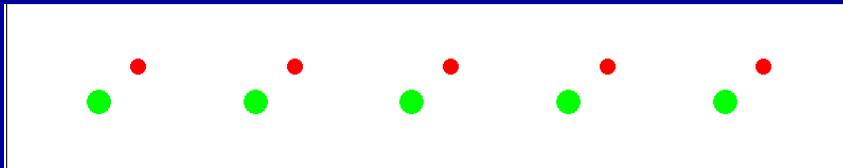
Phonon Detection – Coherent Phonon (coherent vibration of lattice)



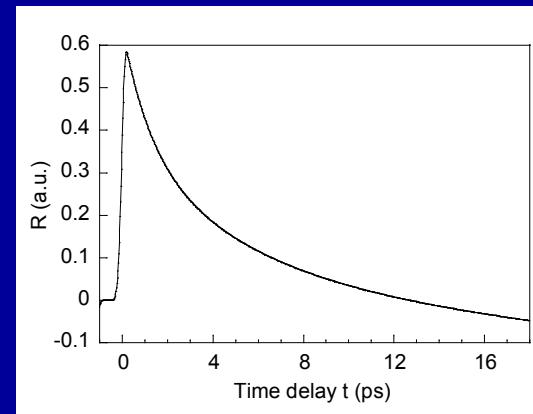
Random thermal vibration



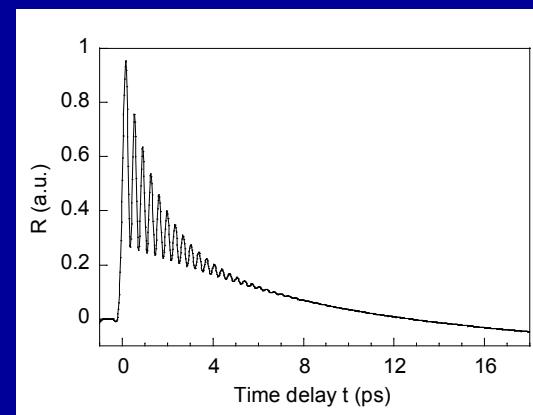
Coherent Phonon - LO



Coherent Phonon - TO

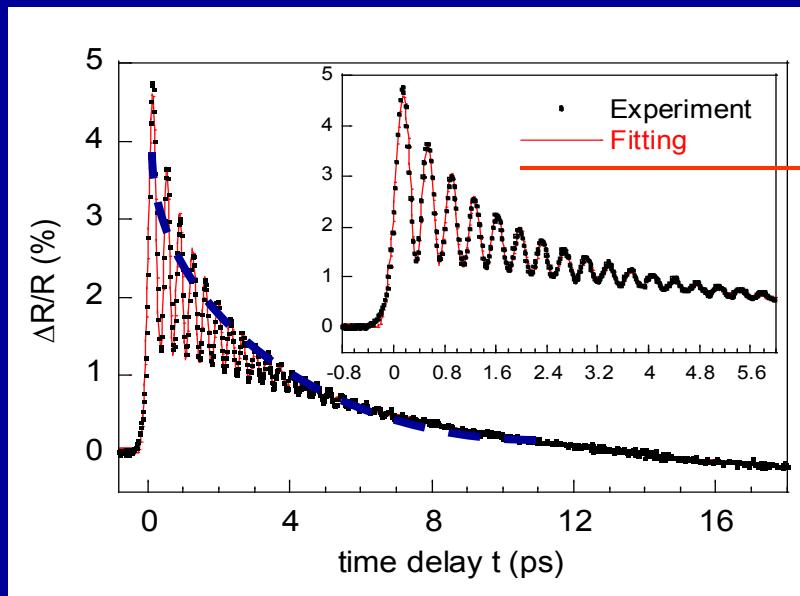


Optical signal when there is **no**
coherent lattice oscillation

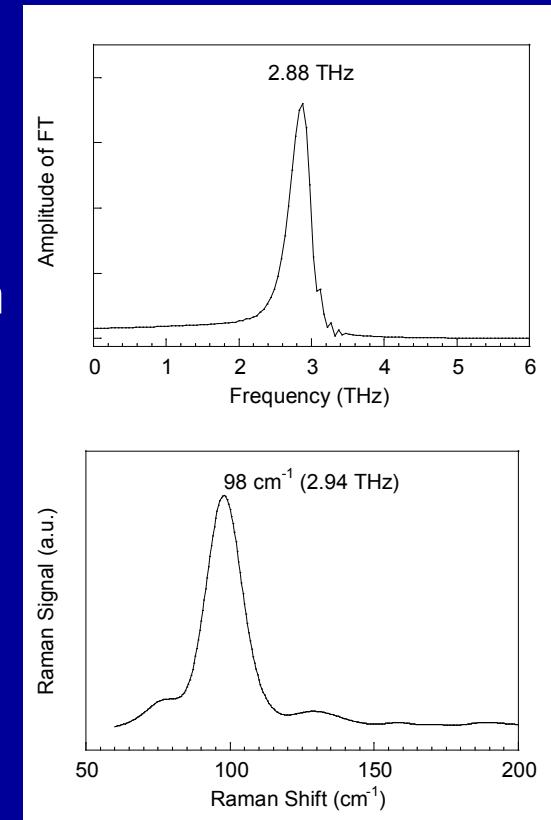


With coherent oscillation

Coherent Phonon Dynamics in Bi

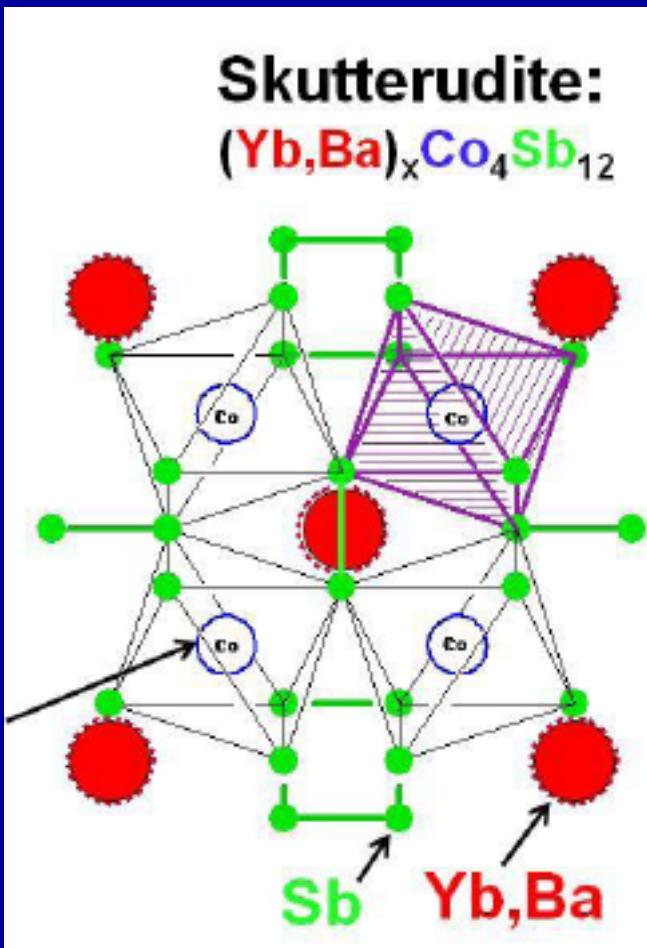


Fourier
transform



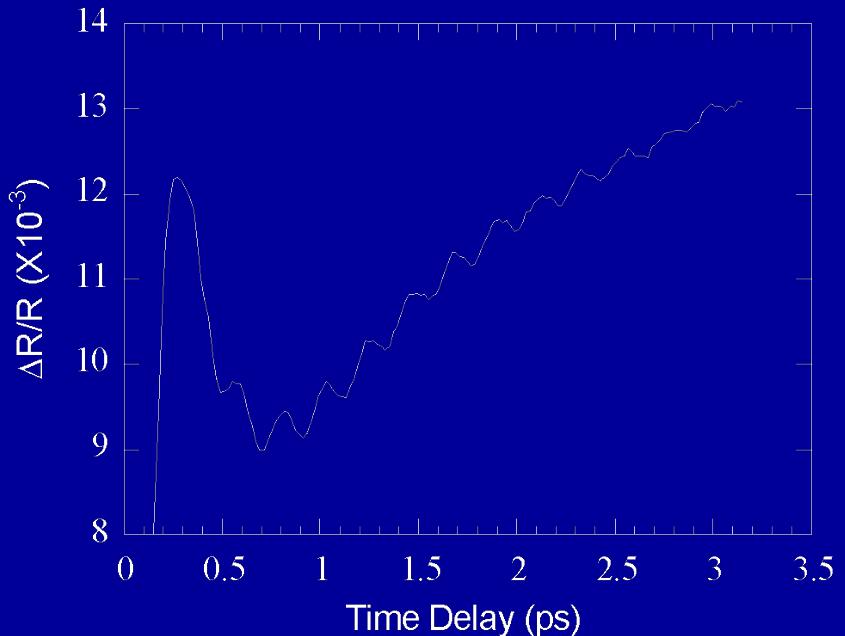
- Rise of the signal: Photon – electron/exciton (charge) coupling
- Decay of the envelope of the signal: electron/exciton (charge) – phonon coupling - heating
- Phonon oscillation and dephasing: Phonon interactions with charges, other phonon modes, impurities, physical boundaries, etc. – all important for energy transport and conversion processes

Filled Antimony Skutterudites



Co

Sb Yb, Ba

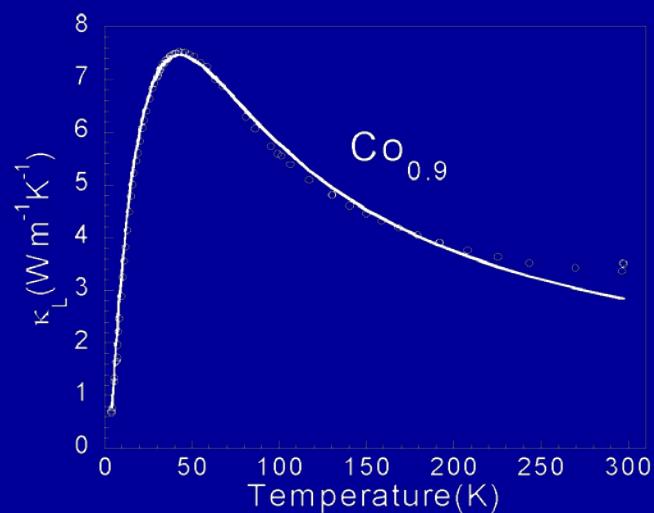
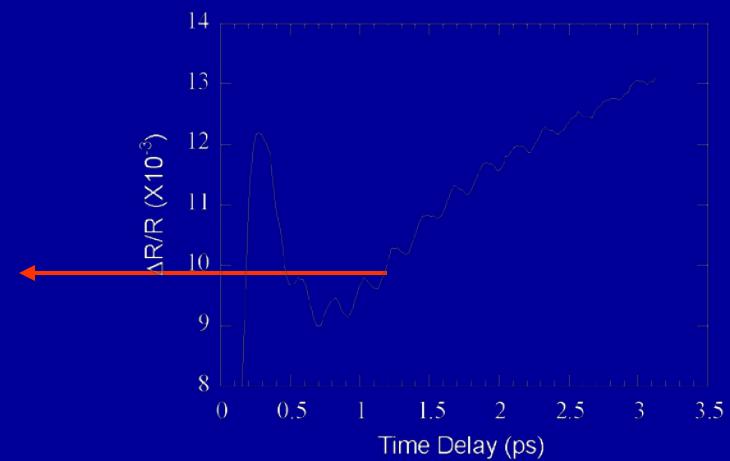
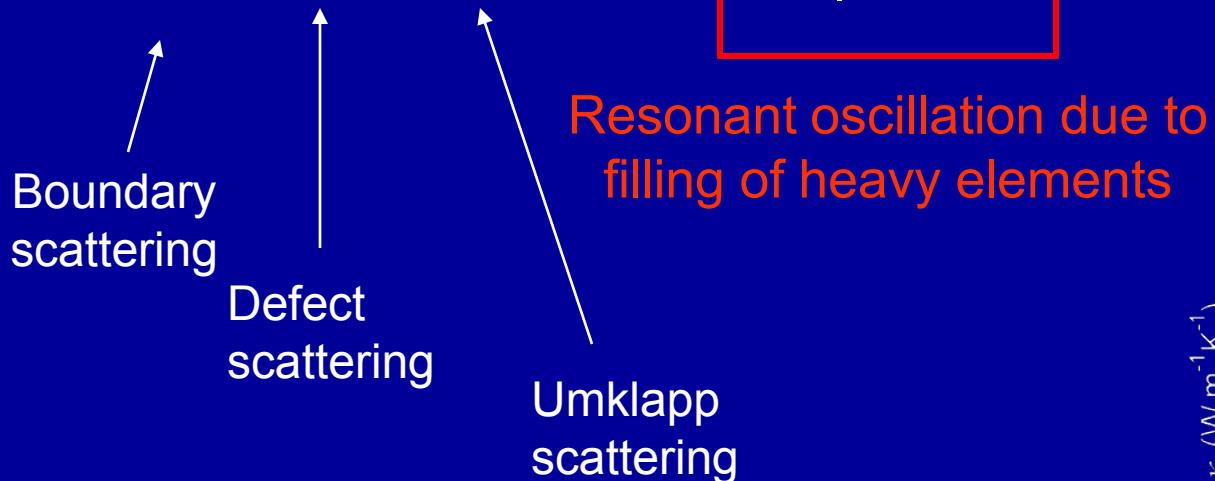


Oscillation due to filling
of guest materials

Lattice Thermal Conductivity Calculation

$$\kappa_L = \frac{k_B}{2\pi^2 v} \left(\frac{k_B}{\hbar}\right)^3 T^3 \int_0^{\theta_D/T} \frac{x^4 e^x}{\tau^{-1}(e^x - 1)} dx$$

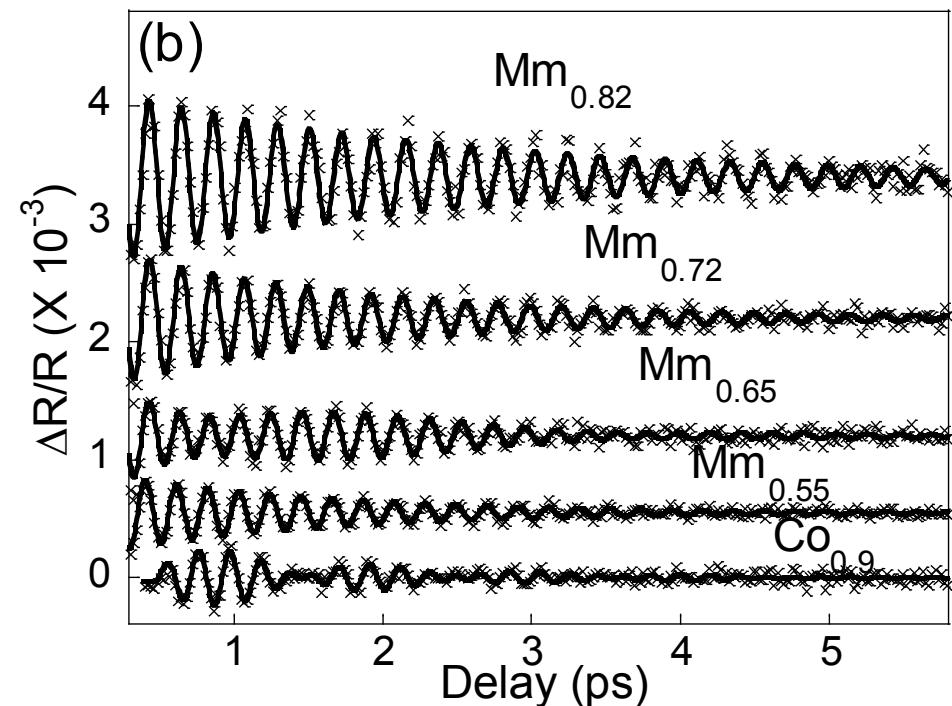
$$\tau^{-1} = \frac{v}{L} + A\omega^4 + B\omega^2 Te^{-\theta_D/3T} + \frac{C\omega^2}{(\omega_0^2 - \omega^2)^2}$$

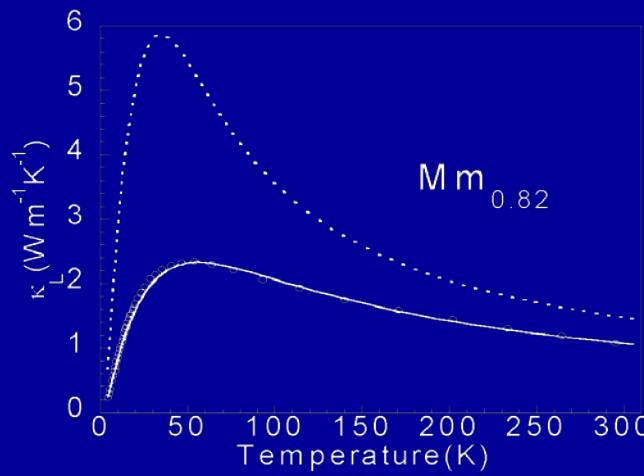
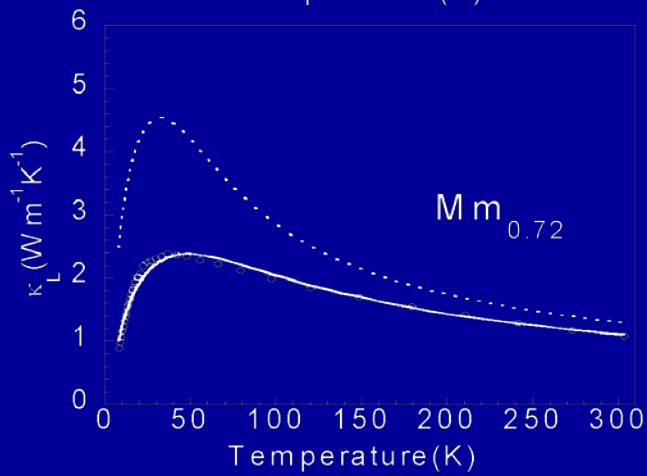
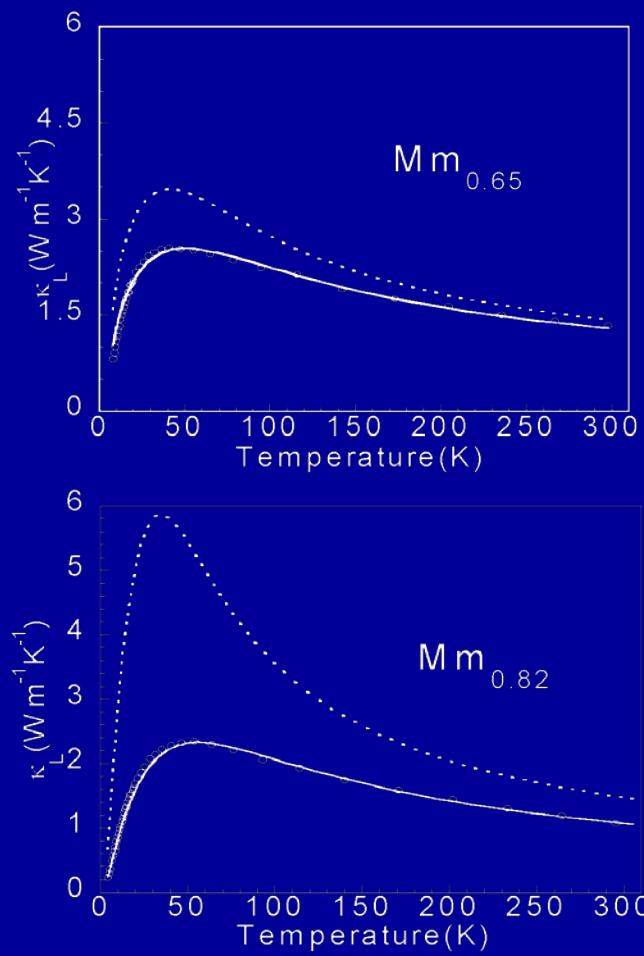
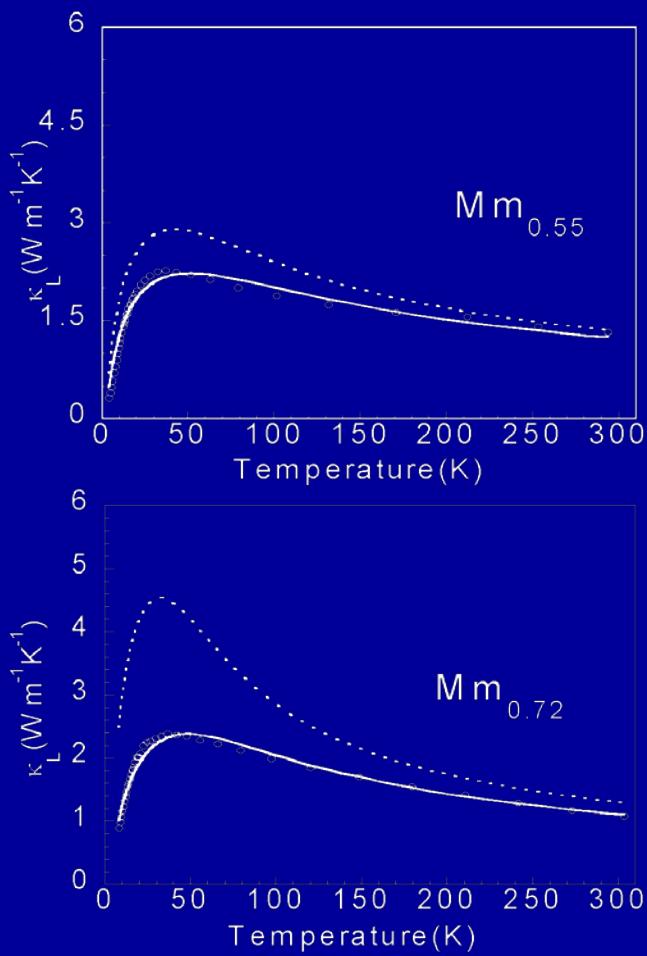


Misch-metal Filled Antimony Skutterudites

Mm: Ce:La:Nd:Pr:Si:Fe:Al:O = 50.75:22.75:16.22:5.72:3.35:0.72:0.50

Nominal representation	Composition
Co _{0.9} (unfilled)	Co _{0.9} Fe _{0.1} Sb ₃
Mm _{0.55}	Mm _{0.55} Fe _{2.44} Co _{1.56} Sb _{11.96}
Mm _{0.65}	Mm _{0.65} Fe _{2.92} Co _{1.08} Sb _{11.98}
Mm _{0.72}	Mm _{0.72} Fe _{3.43} Co _{0.57} Sb _{11.97}
Mm _{0.82}	Mm _{0.82} Fe ₄ Sb _{11.96}



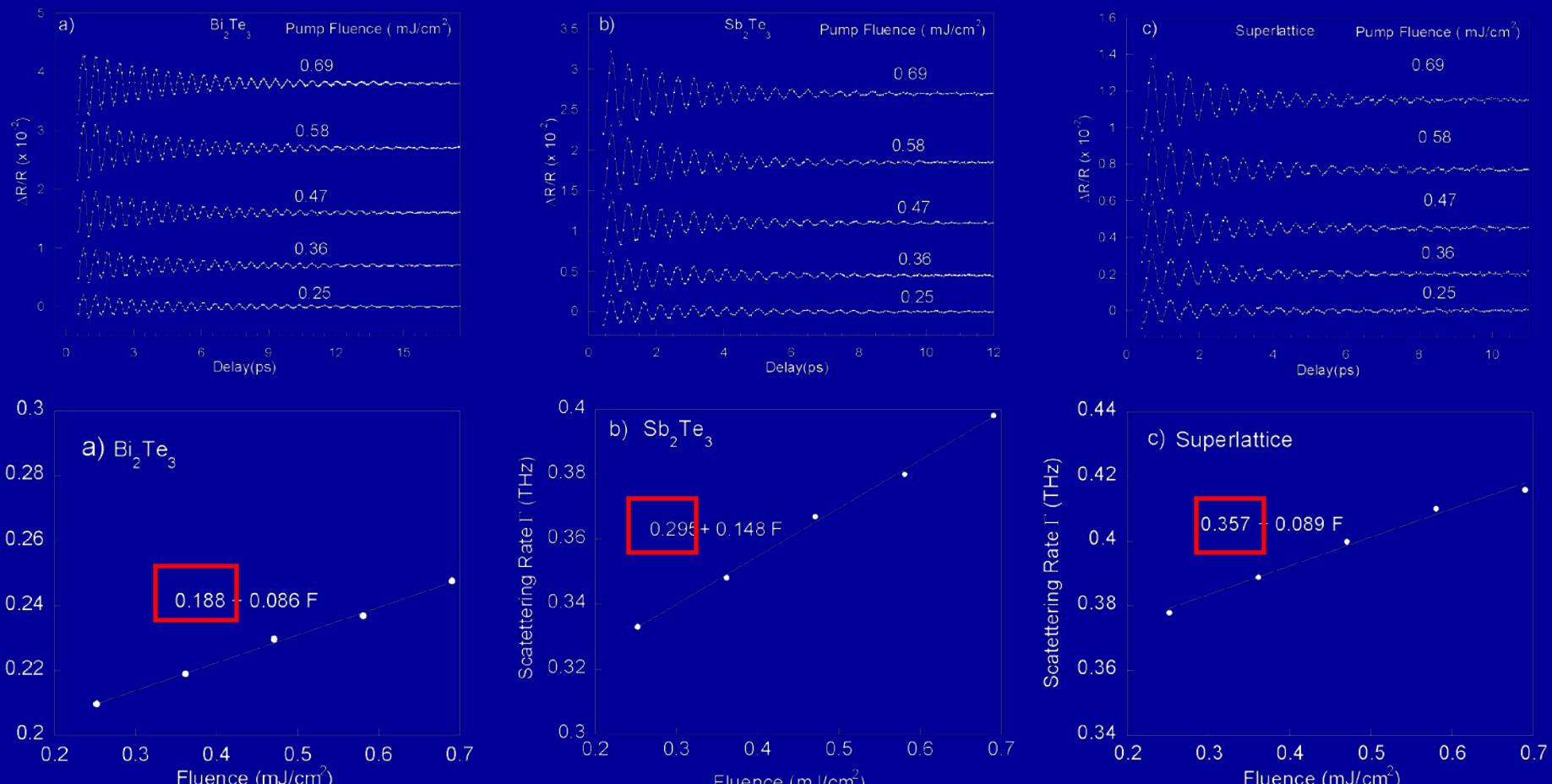


- Computation of κ based on resonant oscillation model and ultrafast measurement results agree well with κ value measured from ~ 0 to 300 K.
- Role of filled material: resonant vibration vs. defect generation

(Phys. Rev. Lett, 2009)



Phonon Scattering in Bi_2Te_3 , Sb_2Te_3 and $\text{Bi}_2\text{Te}_3/\text{Sb}_2\text{Te}_3$ Superlattice



(in collaboration with RTI)

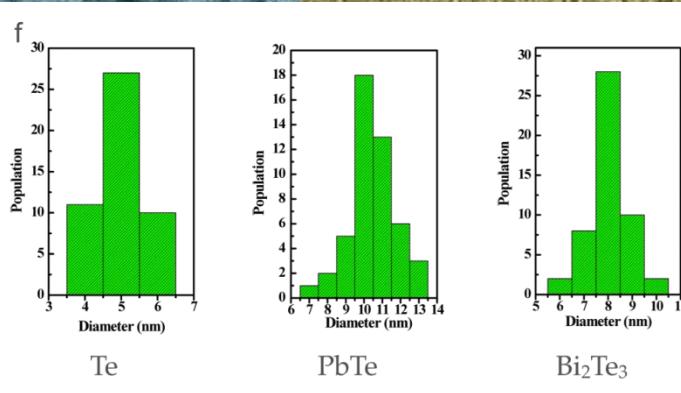
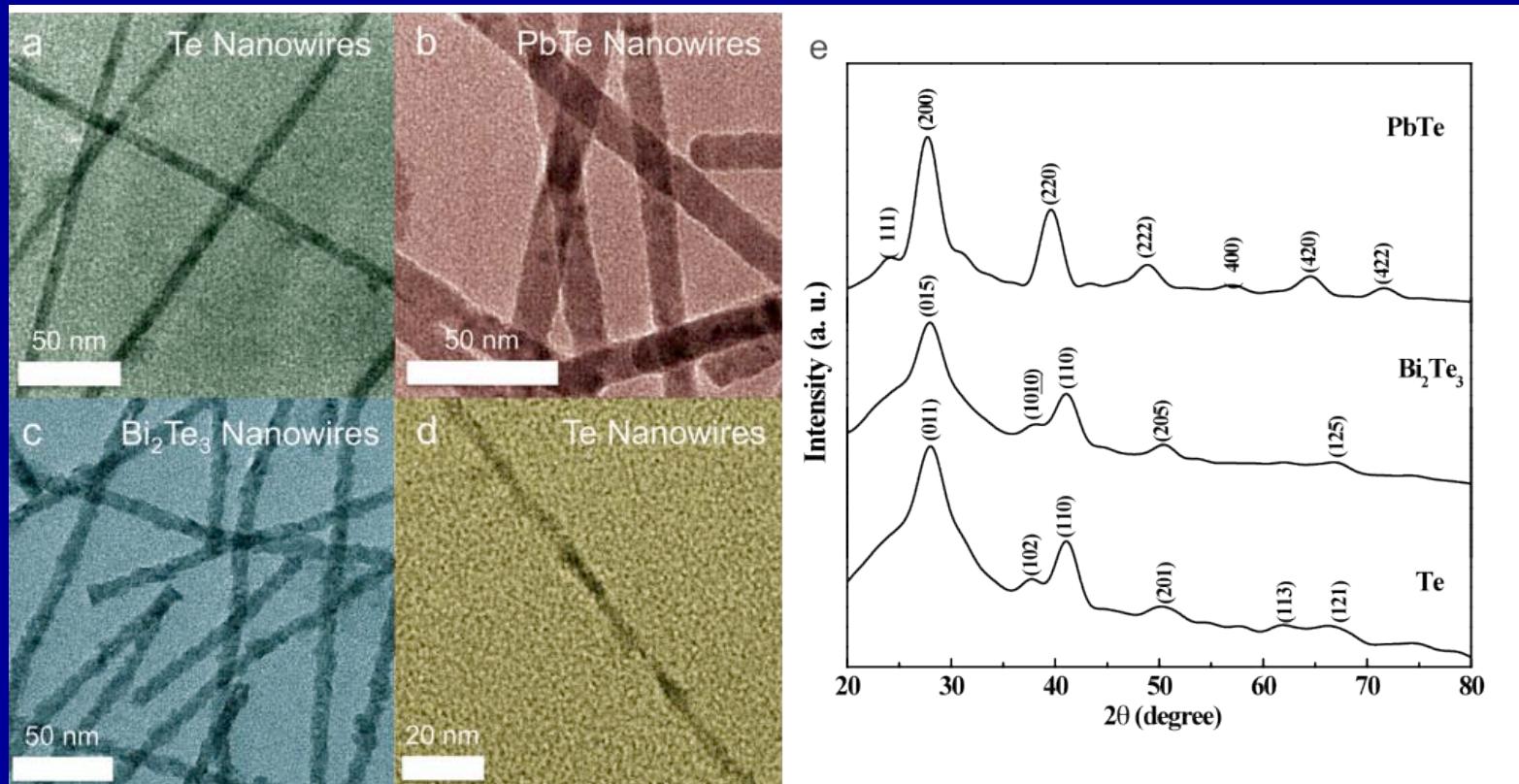


Nanowire TE Materials

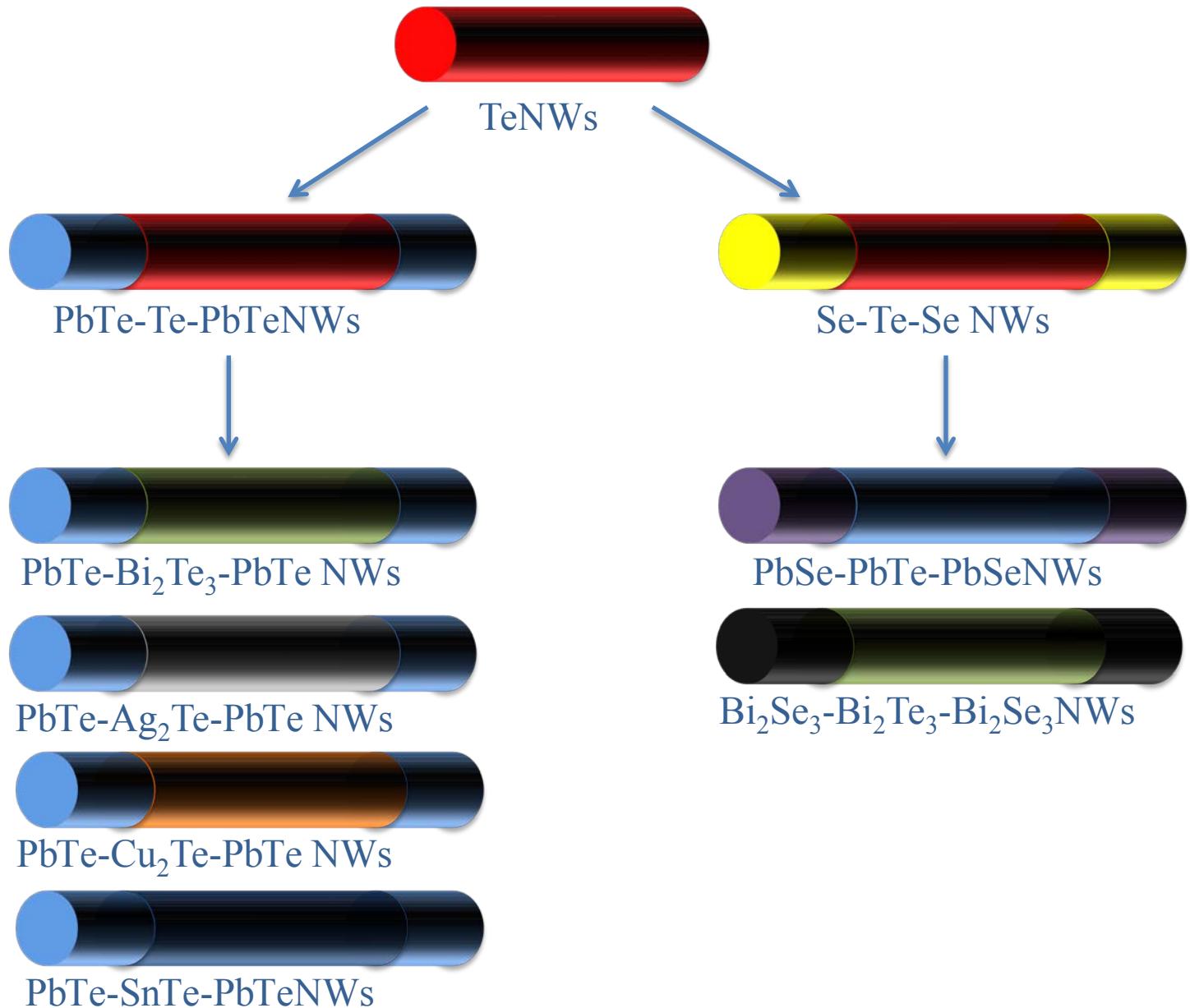
Yue Wu, School of Chemical Engineering



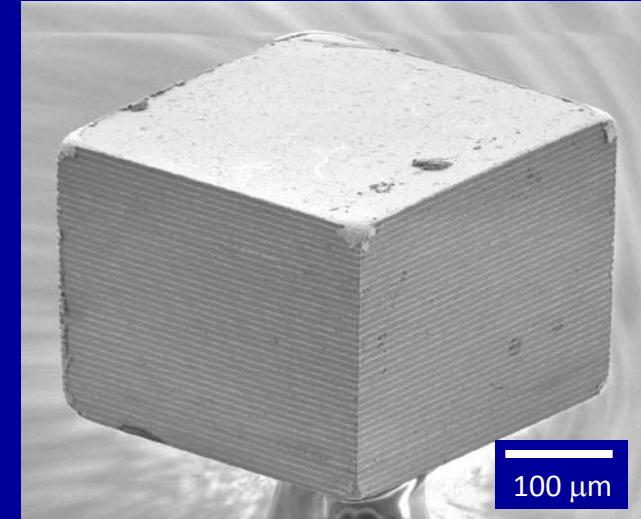
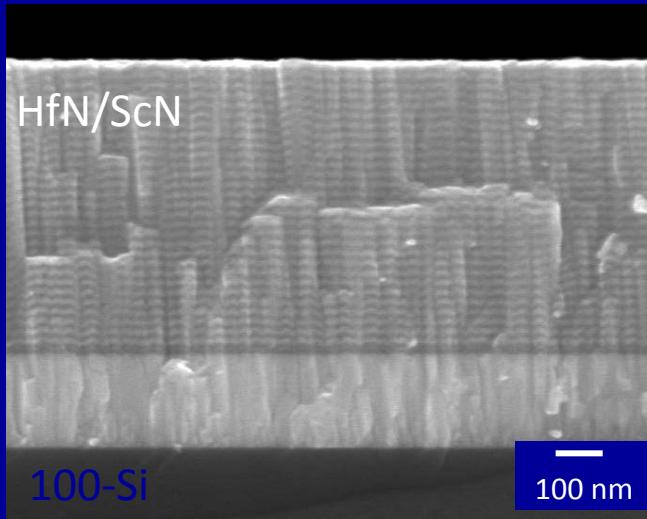
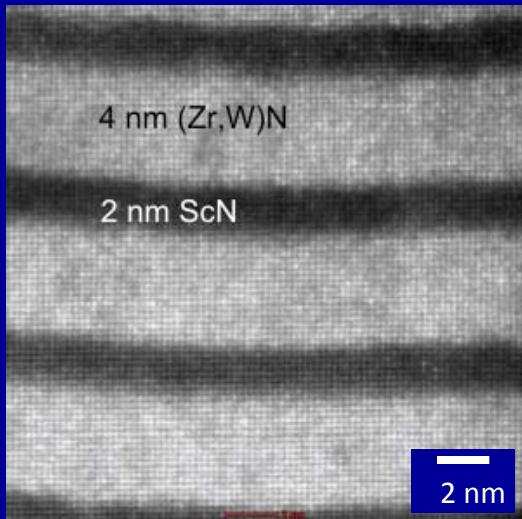
Synthesis of Molecular-scale Chalcogenide Nanowires



Scalable and high yield (93%)



Bulk-like Thermionic Energy Conversion Device Fabricated from Laminated Nanostructured Metal/Semiconductor Superlattices



Co-PI: Tim Sands

Research Associate: Jeremy Schroeder

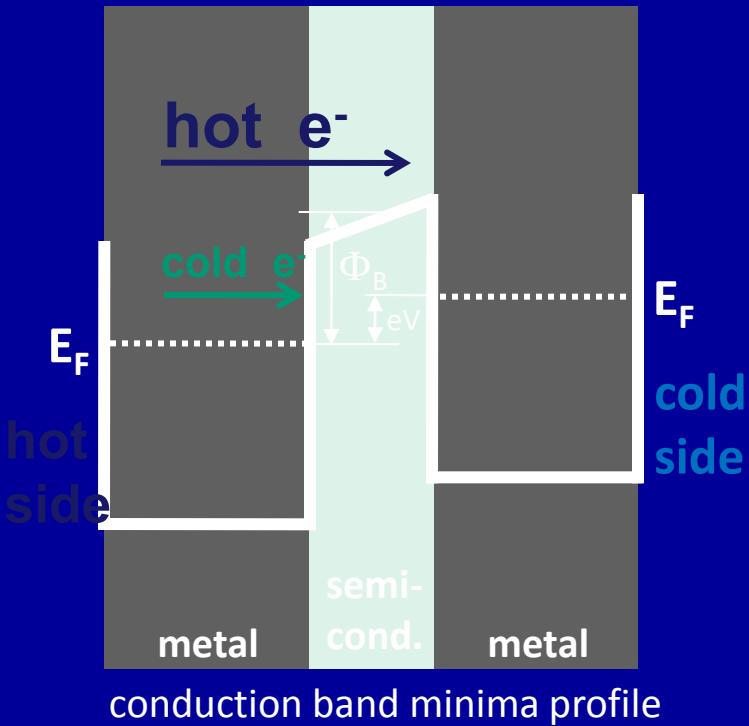
Graduate Student: Bivas Saha



Purdue University

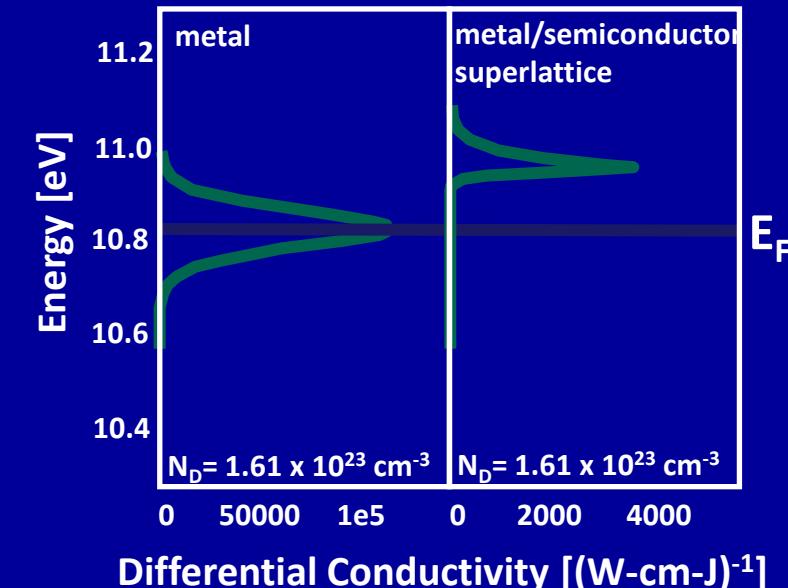
Benefit of M-S superlattice

Thermionic transport

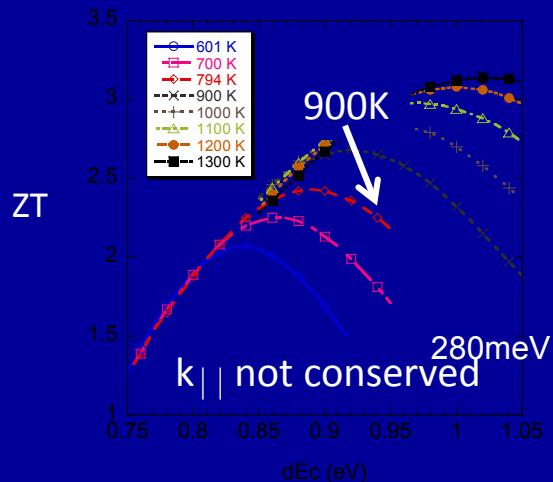


ZT predictions →

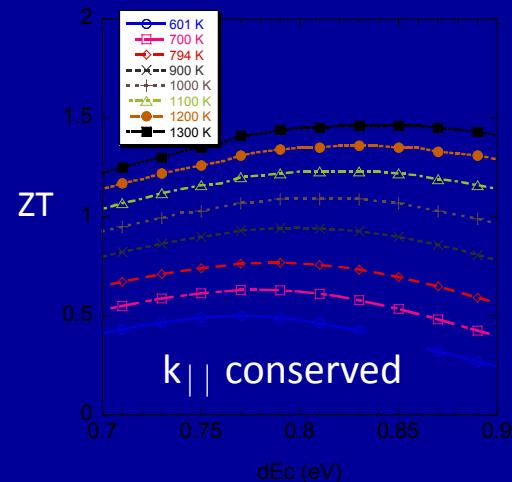
- Experimental data:
 - $\kappa = 1.8 \text{ W/m-K}$
 - $\Phi_B = 280 \text{ meV}$
 - $S = -820 \mu\text{V/K}$



D. Vashaee and A. Shakouri, Phys. Rev. Lett. 92, 106103 (2004)



Zebarjadi et al., J Elect. Mat., (2009)



Laminates

Deposit metal

substrate

5µm polySL

↑
1µm bonding metal
↓

5µm polySL

substrate

Bond

Etch substrate

Laminate bilayers



	Total thickness
TE layers	50µm
Au bonding layers	20µm



Thermal properties

$$\kappa_{TE} = 3 \text{ W/m-K}$$

$$\kappa_{Au} = 300 \text{ W/m-K}$$

$$R_{c,thermal} \approx 7 \times 10^{-8} \text{ K-m}^2/\text{W}$$

Electrical properties

$$\rho_c = 1 \times 10^{-8} \Omega\text{-cm}^2$$

$$\rho_{TE} = 1 \text{ m}\Omega \text{-cm}$$

$$\rho_{Au} = 25 \mu\Omega \text{-cm}$$

TE layers

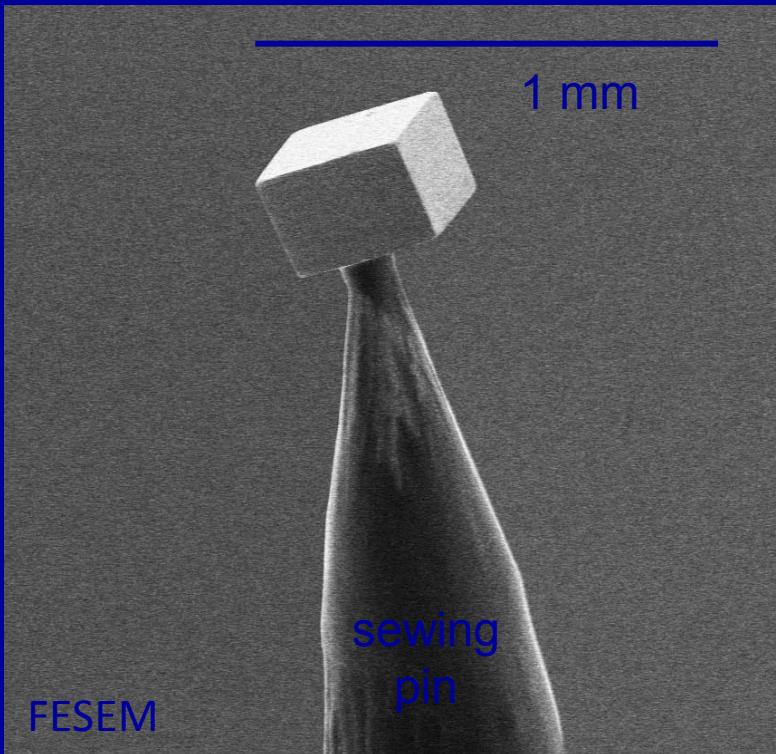
{ 93% of total thermal impedance
96% of total electrical impedance



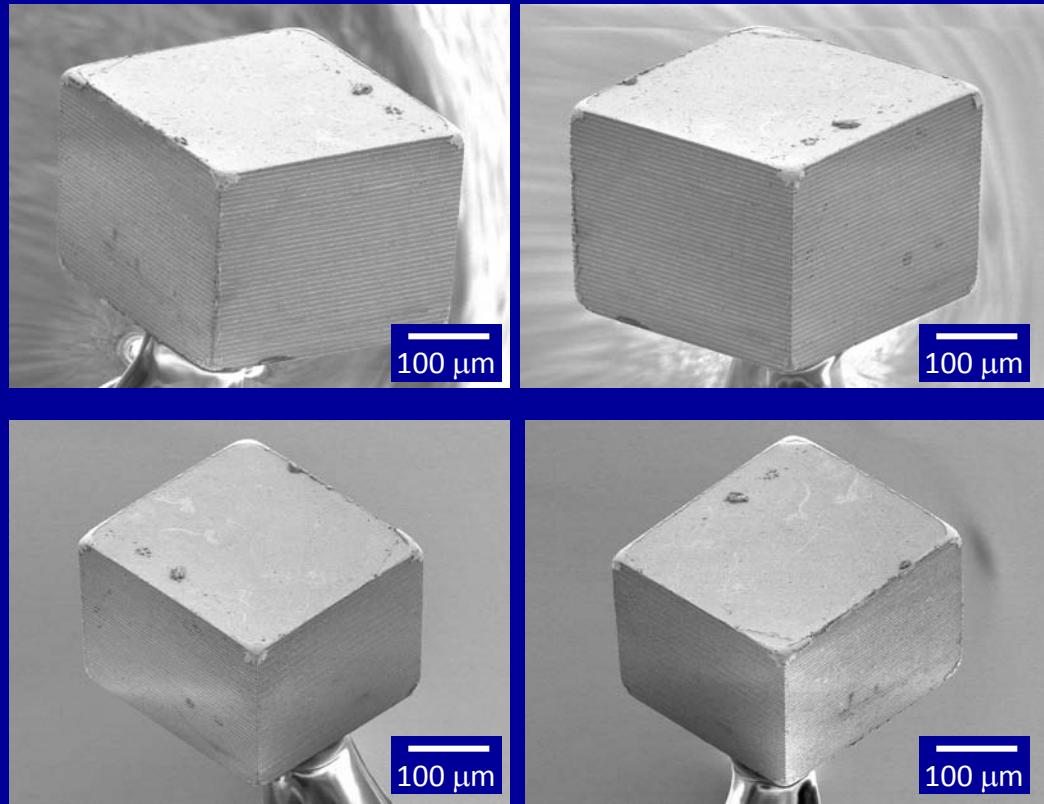
Process requires low metal-nitride/metal-bond contact resistance

Purdue University

Bulk-like laminate



- 40 thermoelectric layers (5 μm each)
- 80 gold layers (1 μm each)
- $\sim 300 \mu\text{m} \times 300 \mu\text{m} \times 280 \mu\text{m}$
- diced and polished (3 μm diamond lapping disc)



SEM of four sides of polished cube

Heat Exchangers for Automotive Exhaust Applications

Professor Steve Heister
School of Aeronautics & Astronautics



Background

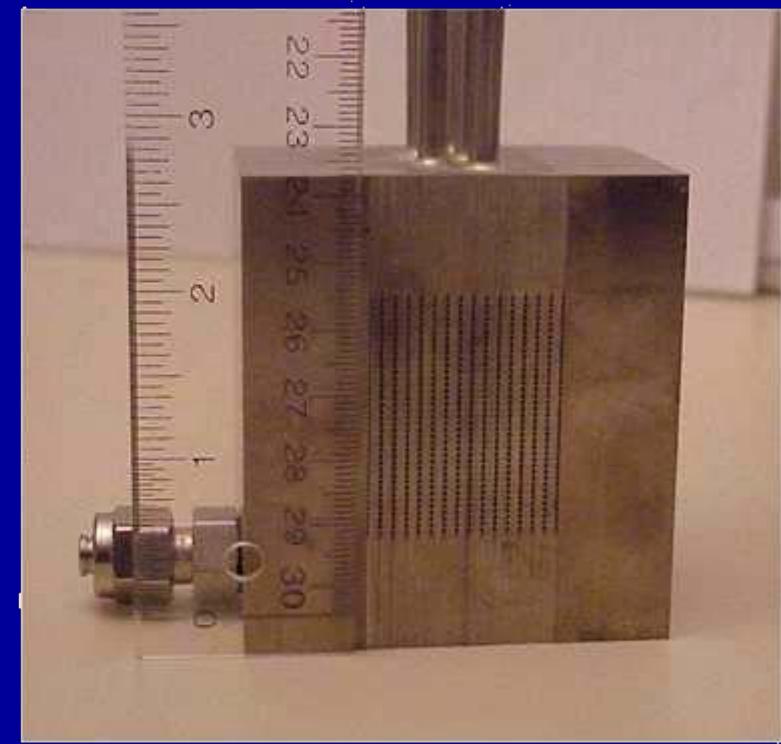
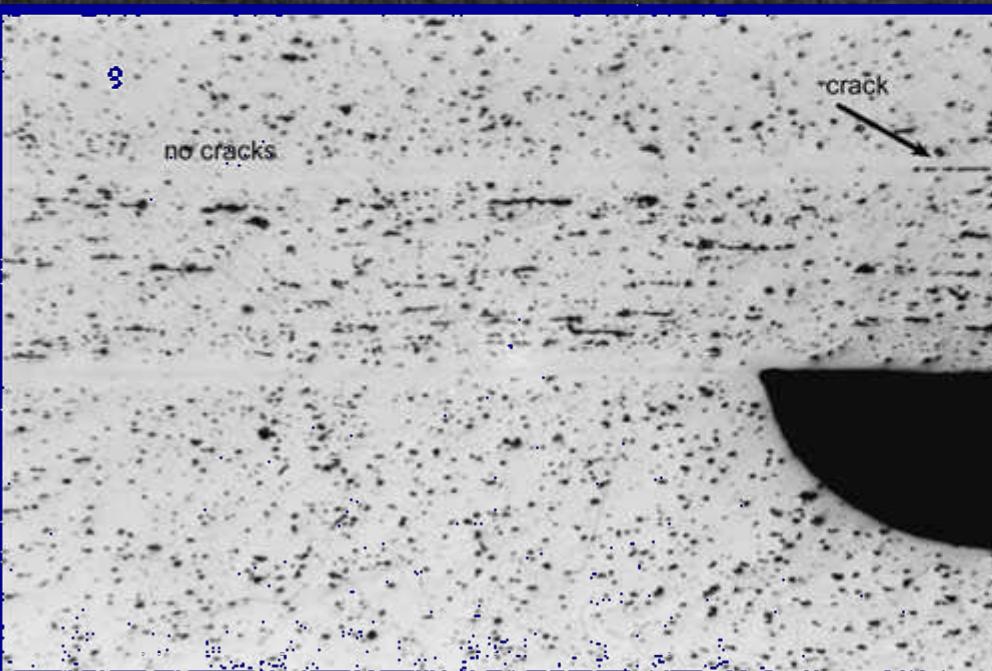
- Rolls-Royce established a University Technology Center (UTC) at Purdue in 2003 to study High Mach Propulsion for aerospace applications
- A key technology to enable high Mach flight is a heat exchanger that cools some compressor exhaust gases for use in turbine blade cooling
 - Air temps 1000-1200F (550-650 C) pressures to 40 bar
 - Fuel temps to 1000F (550 C) at pressures to 90 bar
- UTC has graduated roughly 10 students working in technologies to enable a fuel/air heat exchanger for operation in difficult environments
 - fuel coking/thermal stability
 - tube/shell HEX design
 - plate/fin HEX design
 - heat transfer augmentation



Foil Laminate Construction

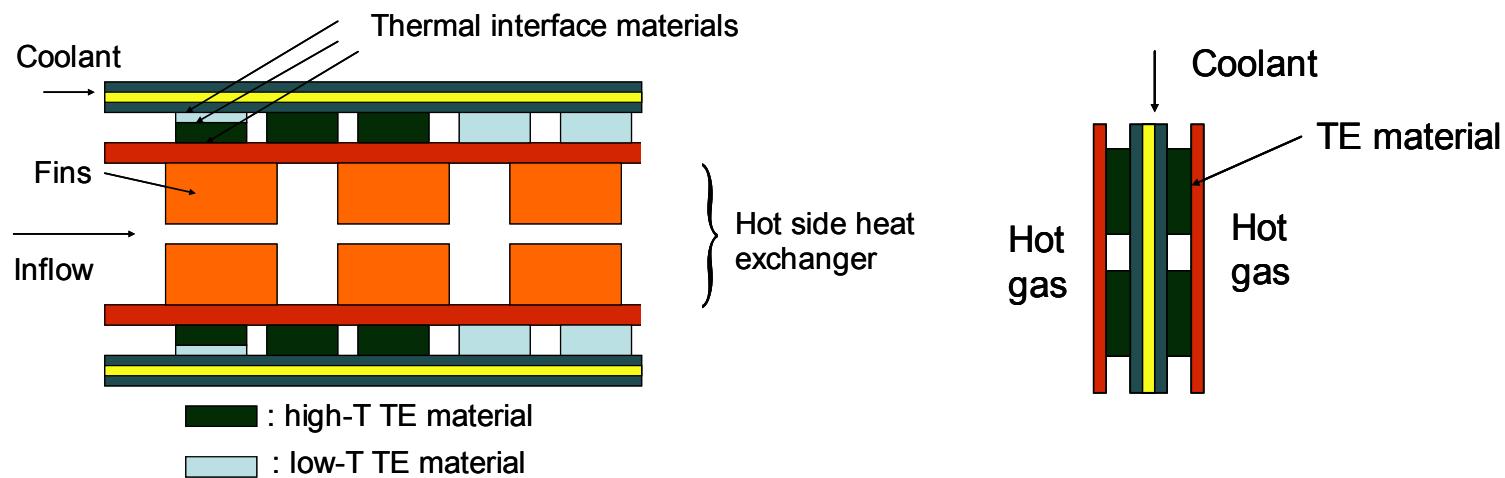
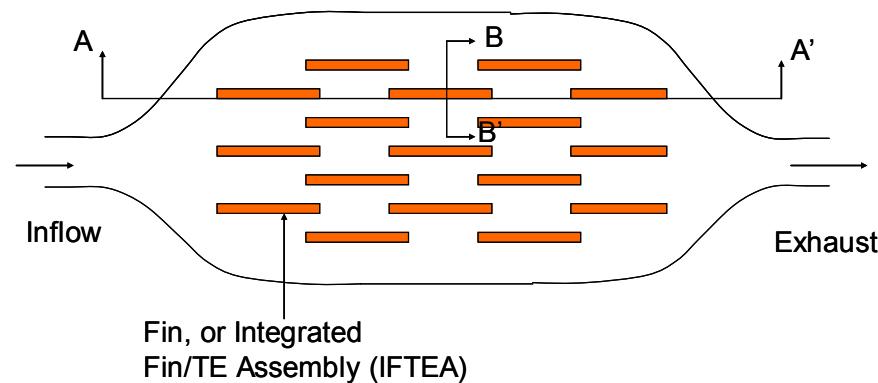
Chemical etching produces microscale flow passages on individual foils.

The foils are then stacked, aligned, and diffusion bonded under heat and pressure.



From "Compact Superalloy Heat Exchangers for Cooled Cooling Air Applications", G. Campbell, J Fryer, Saddleback Aerospace, Turbine Symposium Presentation ca. 2002

Heat Exchanger for Waste Heat Recovery



And many other possible topologies (cylindrical etc.)

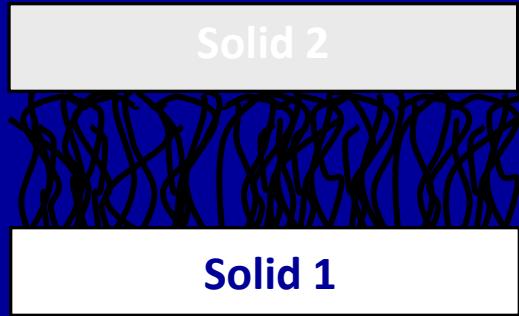
CNT Array Thermal Interfaces Materials

Timothy S. Fisher, Mechanical Engineering

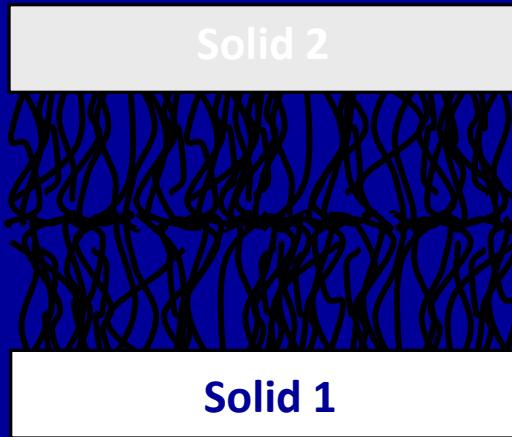


CNT Array Thermal and Electrical Interfaces

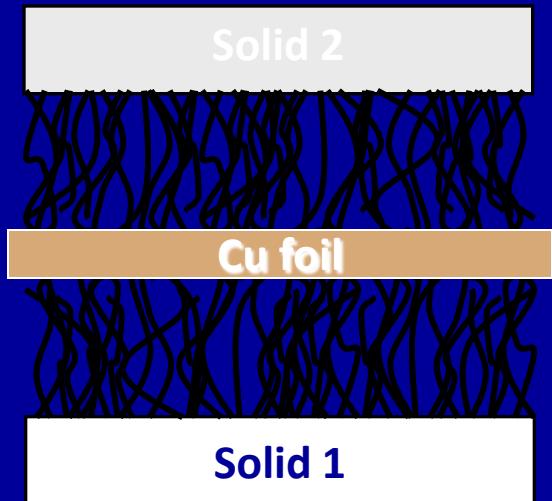
One-sided interface



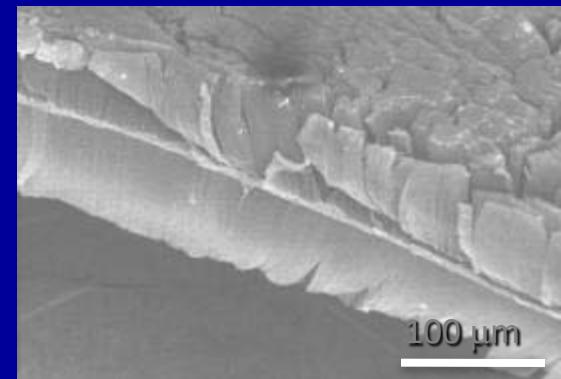
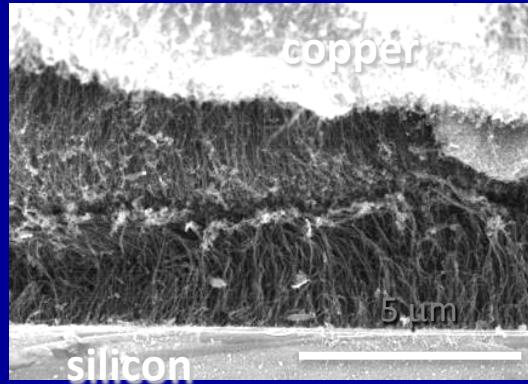
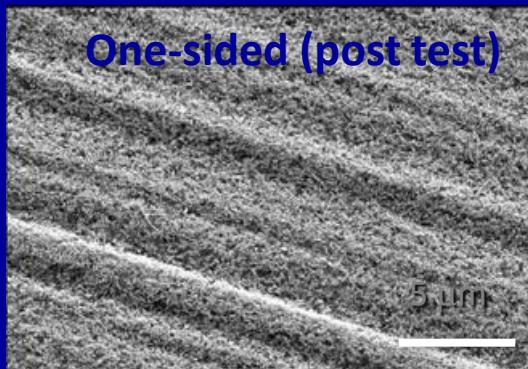
Two-sided interface



CNT/foil interface

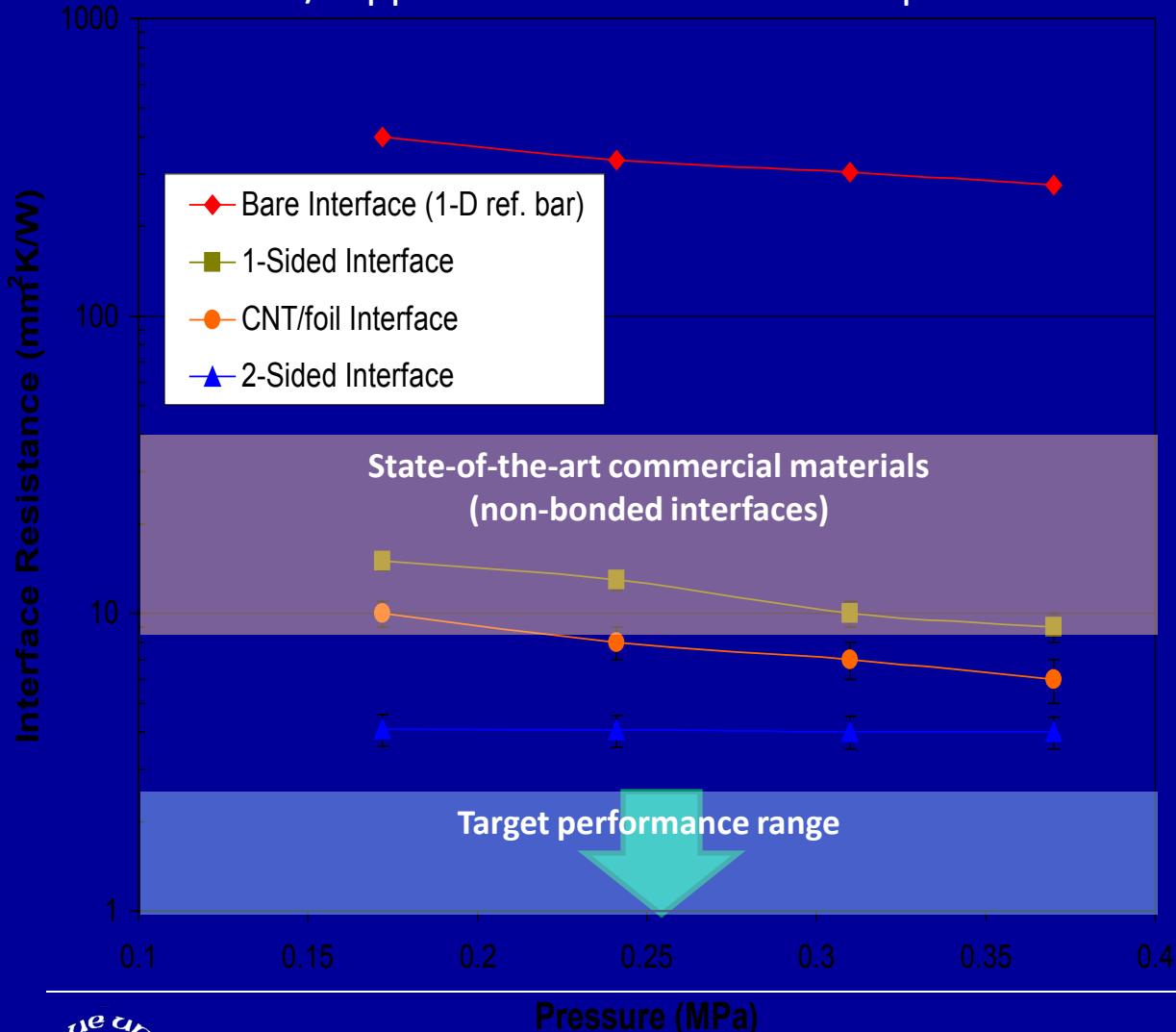


One-sided (post test)



Thermal Interface Results: Summary

silicon/copper substrates at room temperature



References:

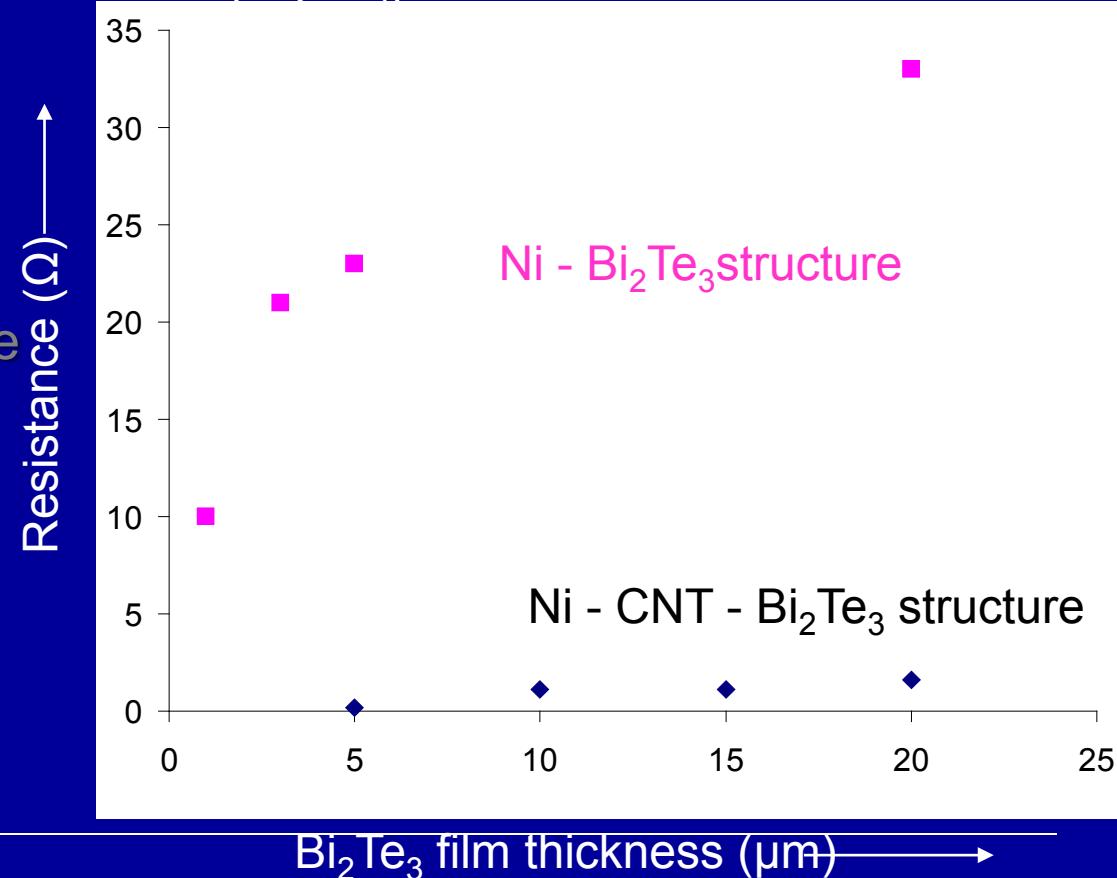
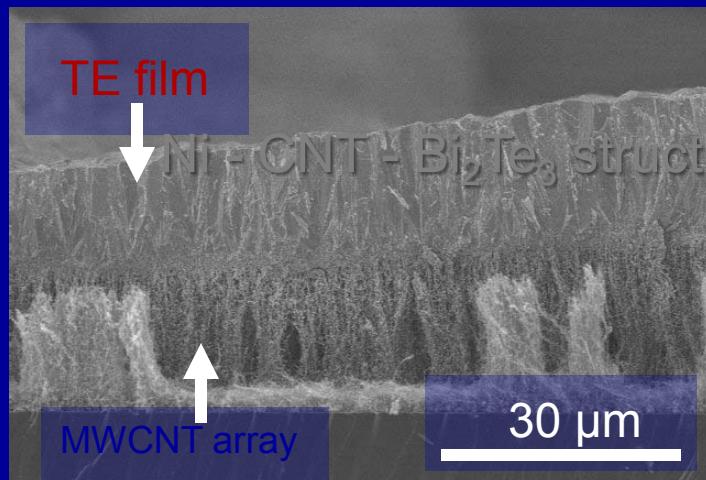
- B.A. Cola, J. Xu, T.S. Fisher, *Int J Heat Mass Transfer*, 52, 3490-3503 (2009).
- B.A. Cola, J. Xu, C. Cheng, H. Hu, X. Xu, and T.S. Fisher, *J. Appl. Phys.* 101, 054313 (2007).
- B.A. Cola, X. Xu, and T.S. Fisher, *Appl. Phys. Lett.* 90, 093513 (2007).
- J. Xu and T.S. Fisher, *Int. J. Heat Mass Trans.* 49, 1658 (2006).
- J. Xu, T.S. Fisher, *IEEE Trans. CPT*, 29, 261 (2006).

CNT Interfaces to Thermoelectrics

Motivation

- Parasitic electrical contact resistance can strongly degrade the efficiency of thermoelectric devices
- Direct electrodeposited thermoelectric (Bi_2Te_3) on CNTs shows reduced interface resistance

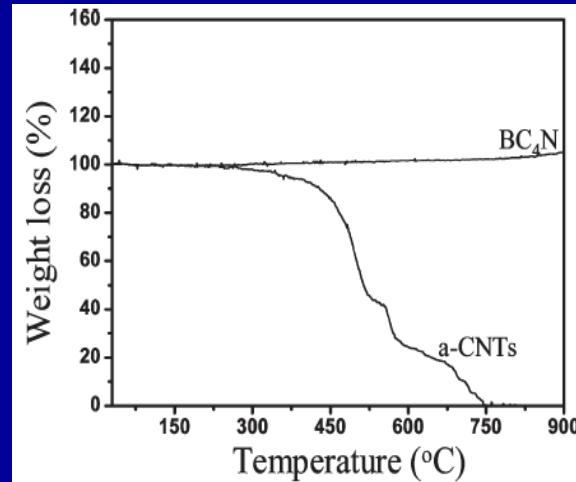
With Sands
group



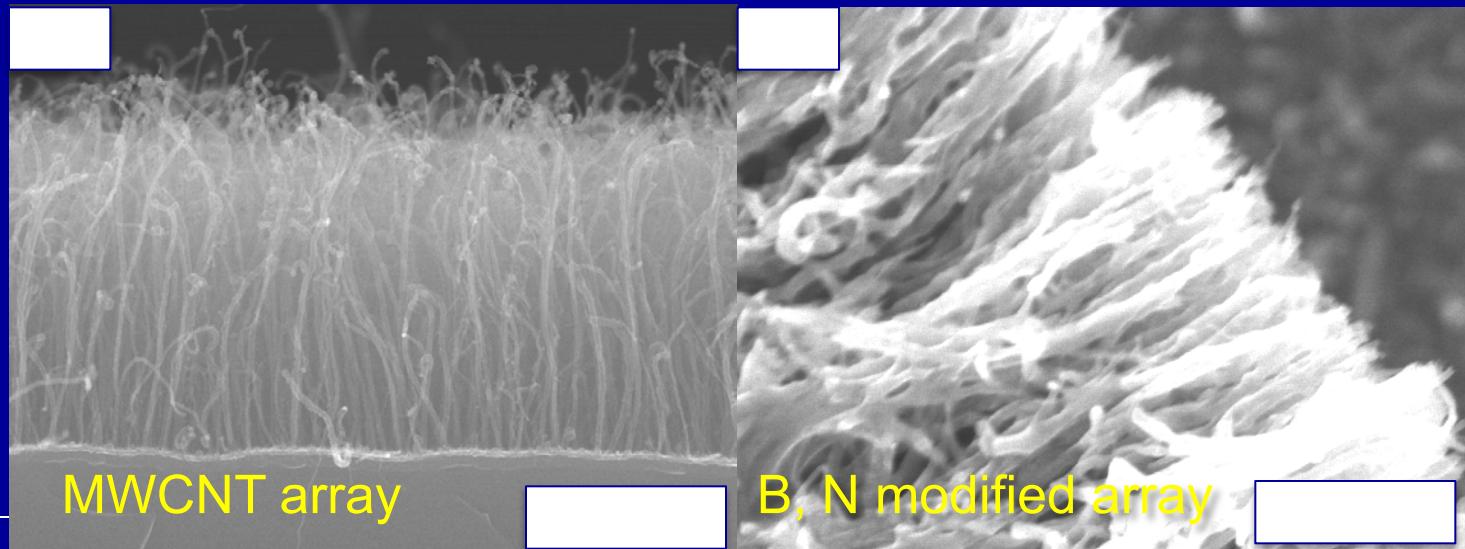
Mishra et al., Adv Mat 21 4280, 2009

Improving Thermal Stability

Raidongia et al. (J. Mater. Chem. 2008, 18, 83-90) demonstrated large improvements in thermal stability of nanotubes by conversion to BC₄N

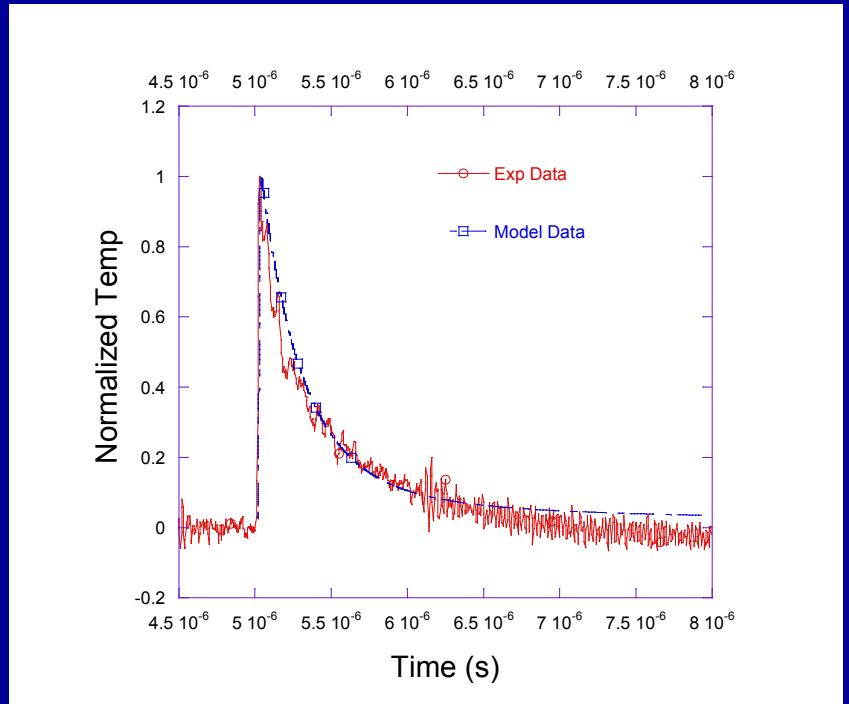


Our recent work:



Thermal Property Characterization: Laser Thermal Reflectance Measurement

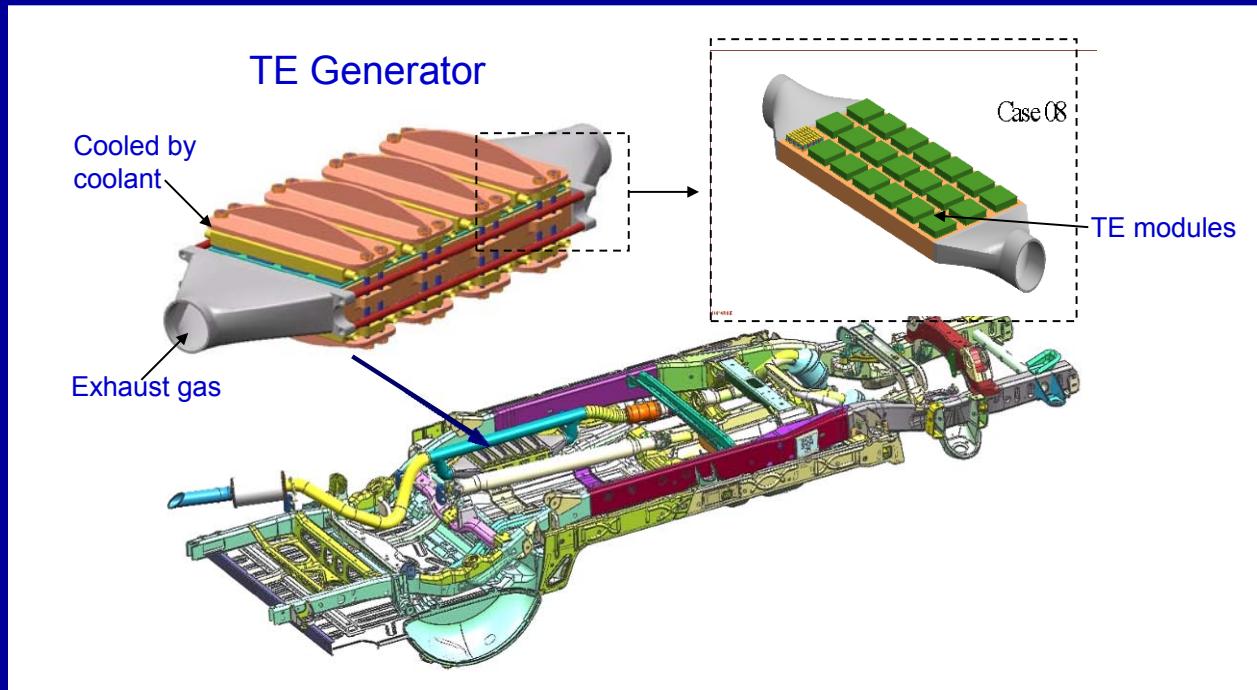
- To determine contact resistance and thermal conductivity
- Temperature up to 700°C
- Use either a femtosecond laser pulse or nanosecond laser pulse for different range of contact resistance
 - femtosecond laser for measuring $R_{ct} < 10^{-6} \text{ m}^2\text{W/K}$
 - nanosecond laser for measuring $R_{ct} > 10^{-7} \text{ m}^2\text{W/K}$



$$R_{ct}=2 \times 10^{-6} \text{ m}^2\text{W/K}$$

TEG System-level Design and Testing

- System level thermal/TEG design (TE modules, thermal interface materials, heat sinks, constraints, etc.)
- Durability
- Cost
- Test strategy, i.e., components vs. sub-systems vs. TEG



(Image courtesy: GM)

- Project started from Jan. 1st, 2011
- Purdue/GM project kick-off meeting on Dec. 13, 2010, at Purdue



We thank the support from:
NSF, PM: Dr. Ted Bergman
DOE, PM: Dr. John Fairbanks, Dr. Tom Avedisian



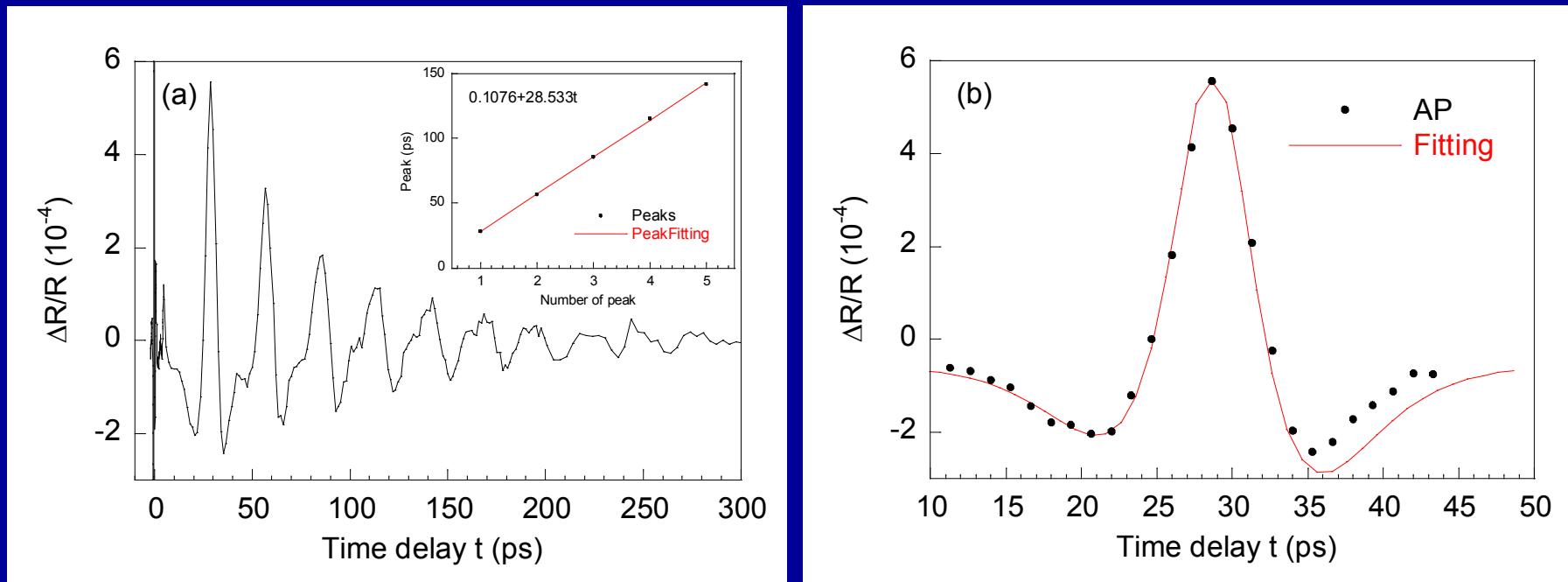


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Coherent Acoustic Phonon



- Wave propagation equation:
- Driving source:
- Temperature increase:

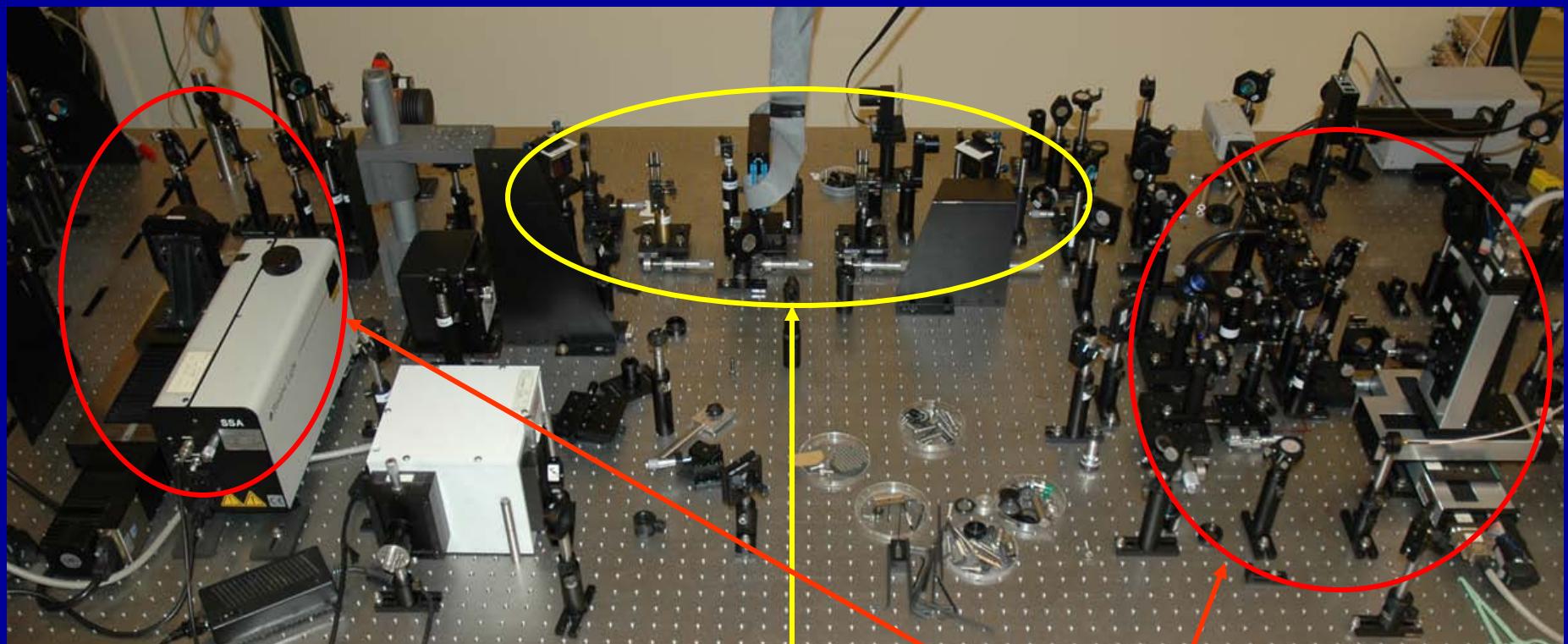
$$\frac{\partial^2 \eta}{\partial t^2} = v^2 \frac{\partial^2 \eta}{\partial z^2} + \frac{1}{\rho} \frac{\partial^2 S}{\partial z^2}$$

$$S = -3 B \beta \Delta T$$

$$\Delta T_{(z,t)} = \Delta T_0 \int_{-\infty}^{\infty} \frac{1}{\sqrt{4\pi\alpha t}} e^{-(z-z')^2/4\alpha t} e^{-|z'|/\xi} dz'$$



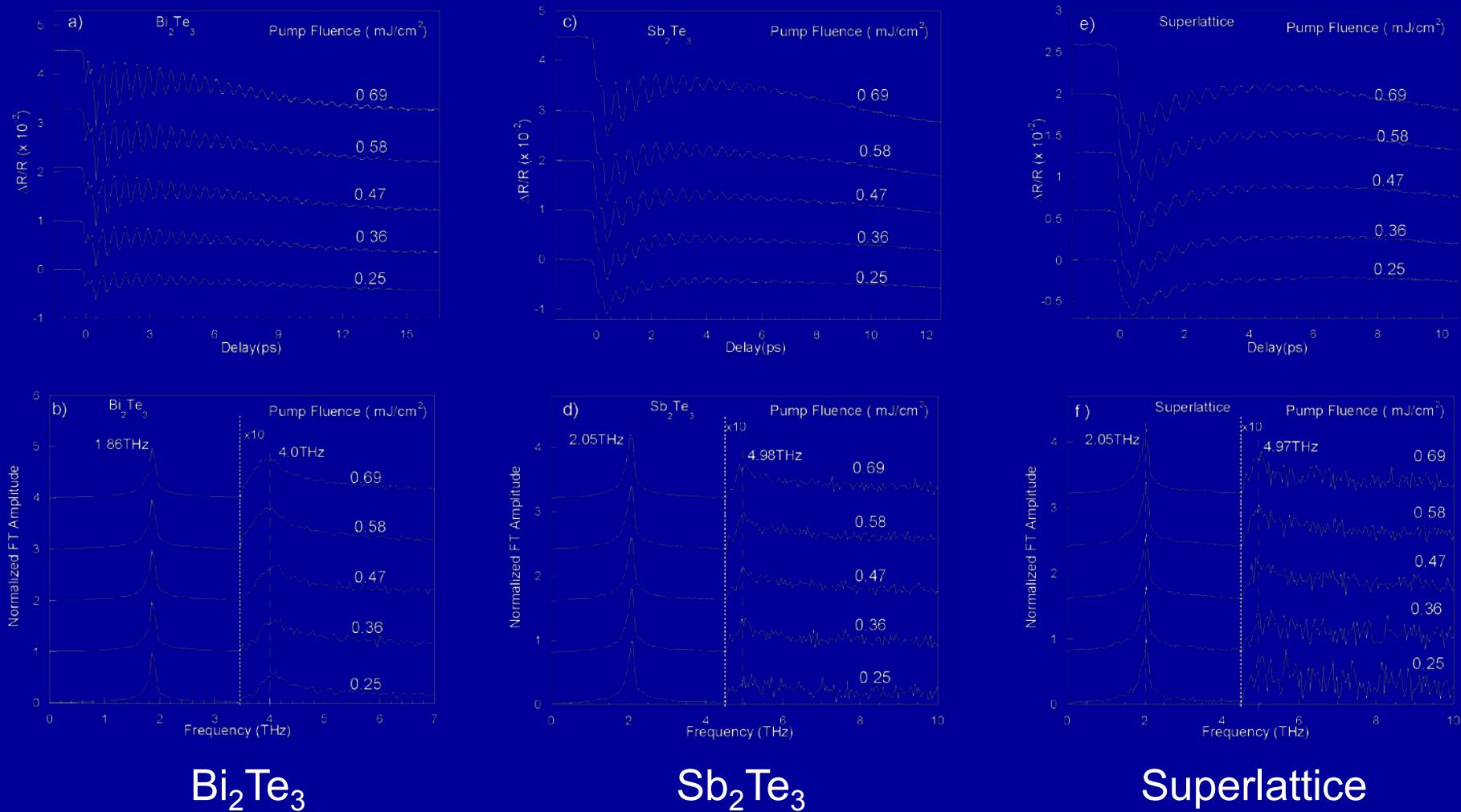
Experimental Setup for Pump-and-probe Measurements



Pulse shaping apparatus

Pump-and-probe set-up

Bi_2Te_3 , Sb_2Te_3 and $\text{Bi}_2\text{Te}_3/\text{Sb}_2\text{Te}_3$ Superlattice



Bi_2Te_3

Sb_2Te_3

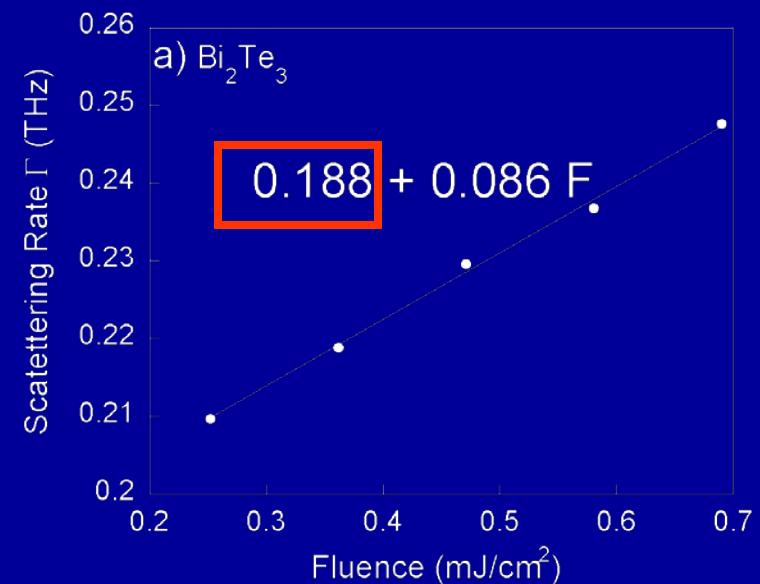
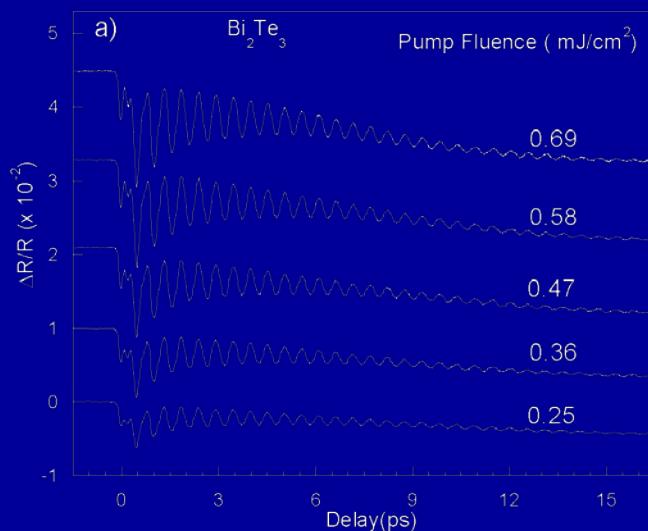
Superlattice



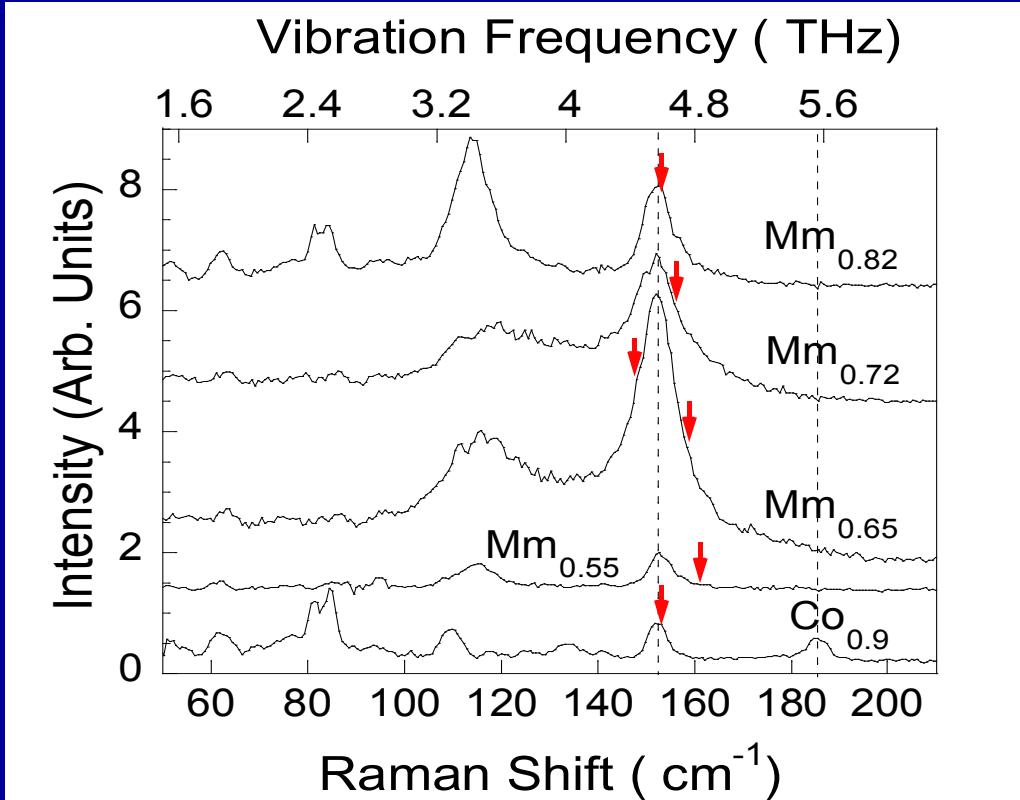
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Phonon Scattering in $\text{Bi}_2\text{Te}_3/\text{Sb}_2\text{Te}_3$ Superlattice

- Scattering of phonon is due to phonon-charge, phonon-phonon, and phonon-boundary/interface interactions.
- Scattering rate of coherent phonon increases linearly with pump fluence.
- Phonon scattering in bulk Bi_2Te_3 , bulk Sb_2Te_3 and $\text{Bi}_2\text{Te}_3/\text{Sb}_2\text{Te}_3$ superlattice is measured and compared.



Ultrafast Measurement vs. Raman



Red arrows:
frequencies from
ultrafast
measurements

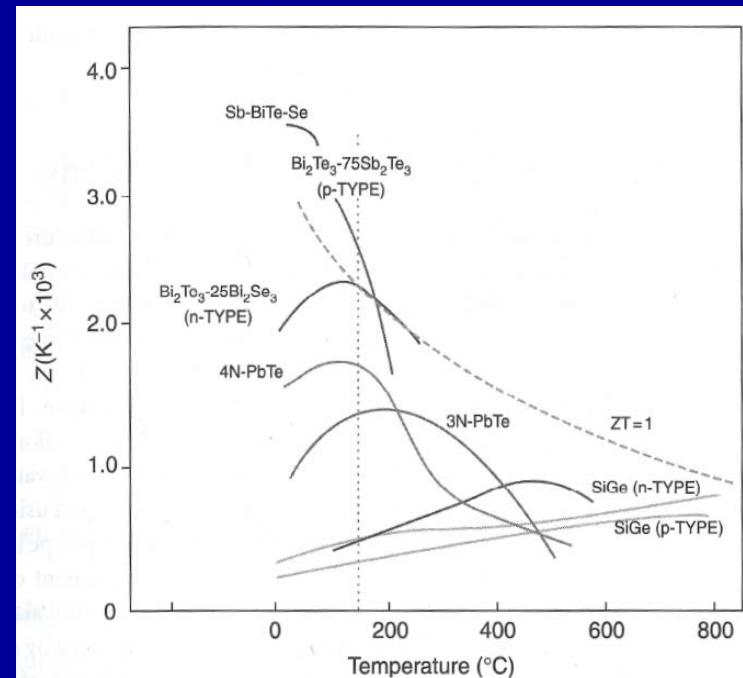
- Raman measurement detects the Sb_4 ring frequency: 4.6 THz
- Ultrafast measured frequencies are different from the Raman frequency, but approach that of Sb_4 ring at high filling ratio, indicating strong interactions between the guest atoms and the lattice (Sb_4 ring).

Figure of merit: $ZT = \frac{S^2 T}{\rho \kappa_{total}} = \frac{S^2 T}{\rho(\kappa_L + \kappa_e)}$

A good thermoelectric material means low electric resistivity ρ and low thermal conductivity κ (phonon glass electron crystal – PGEC)

$ZT \sim 1$ in typical bulk thermal electric materials.

- Carnot efficiency: $\eta = \frac{T_{cold}}{T_{hot} - T_{cold}}$
- $ZT = 1$ corresponds to $\eta = 10\%$
- $ZT = 4$ corresponds to $\eta = 30\%$
- Home refrigerator: $\eta \sim 30\%$
- $\text{Bi}_2\text{Te}_3/\text{Sb}_2\text{Te}_3$ Superlattice: $ZT = 2.4$



Rowe, Thermoelectrics Handbook:
Macro to Nano, CRC Press (2006).

- A systematic study of the effect of phonon scattering in TE materials, and the resulting thermal conductivity reduction.
- Effect of filling ratio of misch metal in different family of skutterudites.
- A theoretical understanding on the effect of the rattling behavior of the filled elements.

